MOSFETs Silicon N-Channel MOS (π-MOSVII)

# TK8P25DA

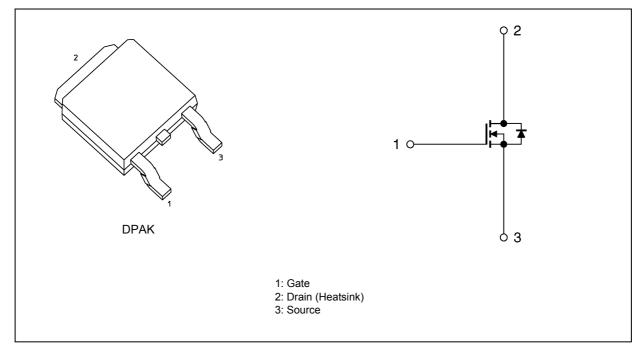
### 1. Applications

• Switching Voltage Regulators

#### 2. Features

- (1) Low drain-source on-resistance:  $R_{DS(ON)} = 0.41 \Omega$  (typ.)
- (2) Low leakage current:  $I_{DSS} = 10 \ \mu A \ (max) \ (V_{DS} = 250 \ V)$
- (3) Enhancement mode:  $V_{th}$  = 1.5 to 3.5 V ( $V_{DS}$  = 10 V,  $I_D$  = 1 mA)

#### 3. Packaging and Internal Circuit



#### 4. Absolute Maximum Ratings (Note) ( $T_a = 25^{\circ}C$ unless otherwise specified)

Characteristics	Symbol	Rating	Unit	
Drain-source voltage		V <sub>DSS</sub>	250	V
Gate-source voltage		V <sub>GSS</sub>	±20	
Drain current (DC)	(Note 1)	Ι <sub>D</sub>	7.5	А
Drain current (pulsed)	(Note 1)	I <sub>DP</sub>	30	
Power dissipation	(T <sub>c</sub> = 25°C)	PD	55	W
Single-pulse avalanche energy	(Note 2)	E <sub>AS</sub>	45	mJ
Avalanche current	(Note 3)	I <sub>AR</sub>	7.5	A
Reverse drain current (DC)	(Note 1)	I <sub>DR</sub>	7.5	
Reverse drain current (pulsed)	(Note 1)	I <sub>DRP</sub>	30	
Channel temperature		T <sub>ch</sub>	150	°C
Storage temperature		T <sub>stg</sub>	-55 to 150	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

#### 5. Thermal Characteristics

Characteristics	Symbol	Max	Unit
Channel-to-case thermal resistance	R <sub>th(ch-c)</sub>	2.27	°C/W
Channel-to-ambient thermal resistance	R <sub>th(ch-a)</sub>	125	

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2:  $V_{DD}$  = 50 V,  $T_{ch}$  = 25°C (initial), L = 1.33 mH,  $R_G$  = 25  $\Omega$ ,  $I_{AR}$  = 7.5 A

Note 3: Repetitive rating; pulse width limited by maximum channel temperature

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

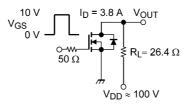
#### 6. Electrical Characteristics

### 6.1. Static Characteristics (Ta = 25°C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I <sub>GSS</sub>	$V_{GS}$ = ±20 V, $V_{DS}$ = 0 V	_	_	±1	μA
Drain cut-off current	I <sub>DSS</sub>	V <sub>DS</sub> = 250 V, V <sub>GS</sub> = 0 V	_	_	10	
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V	250	—	—	V
Gate threshold voltage	V <sub>th</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1 mA	1.5	_	3.5	
Drain-source on-resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 3.8 A		0.41	0.5	Ω

### 6.2. Dynamic Characteristics ( $T_a = 25^{\circ}C$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 100 V, V <sub>GS</sub> = 0 V, f = 1 MHz	_	550	—	pF
Reverse transfer capacitance	C <sub>rss</sub>		_	5.1	_	
Output capacitance	C <sub>oss</sub>		_	40	_	
Gate resistance	r <sub>g</sub>	V <sub>DS</sub> = OPEN, f = 1 MHz	_	5.8	_	Ω
Switching time (rise time)	t <sub>r</sub>	See Figure 6.2.1.	_	28	_	ns
Switching time (turn-on time)	t <sub>on</sub>		_	32	_	
Switching time (fall time)	t <sub>f</sub>			16	_	
Switching time (turn-off time)	t <sub>off</sub>		_	66	_	



Duty  $\leq$  1%, t<sub>w</sub> = 10  $\mu$ s

Fig. 6.2.1 Switching Time Test Circuit

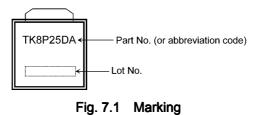
### 6.3. Gate Charge Characteristics ( $T_a = 25^{\circ}C$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	$V_{DD} \approx 200 \text{ V},  V_{GS} \text{ = } 10  \text{V},  \text{I}_{\text{D}} \text{ = } 7.5  \text{A}$	_	16	—	nC
Gate-source charge 1	Q <sub>gs1</sub>		_	3.3	_	
Gate-drain charge	Q <sub>gd</sub>		_	5.3	_	

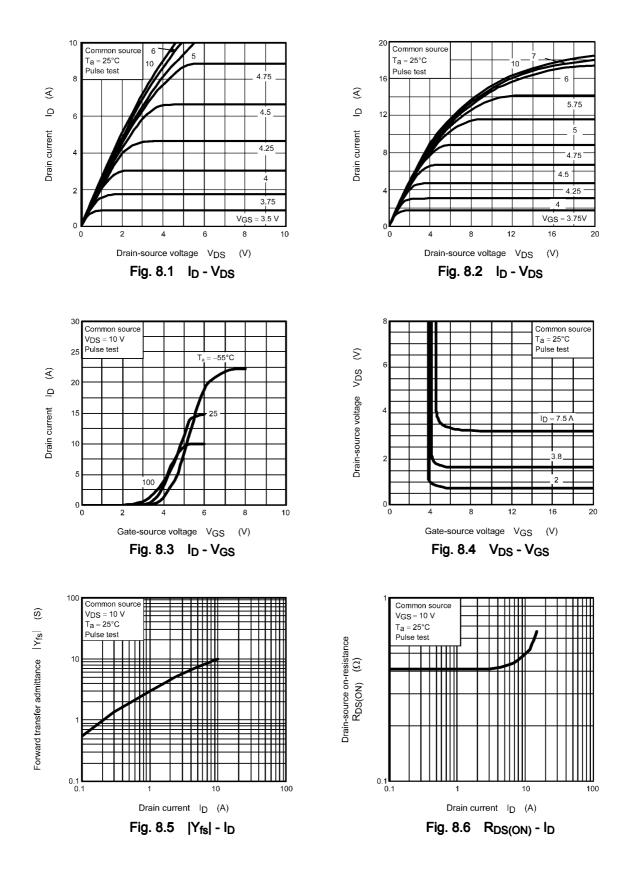
### 6.4. Source-Drain Characteristics ( $T_a = 25^{\circ}C$ unless otherwise specified)

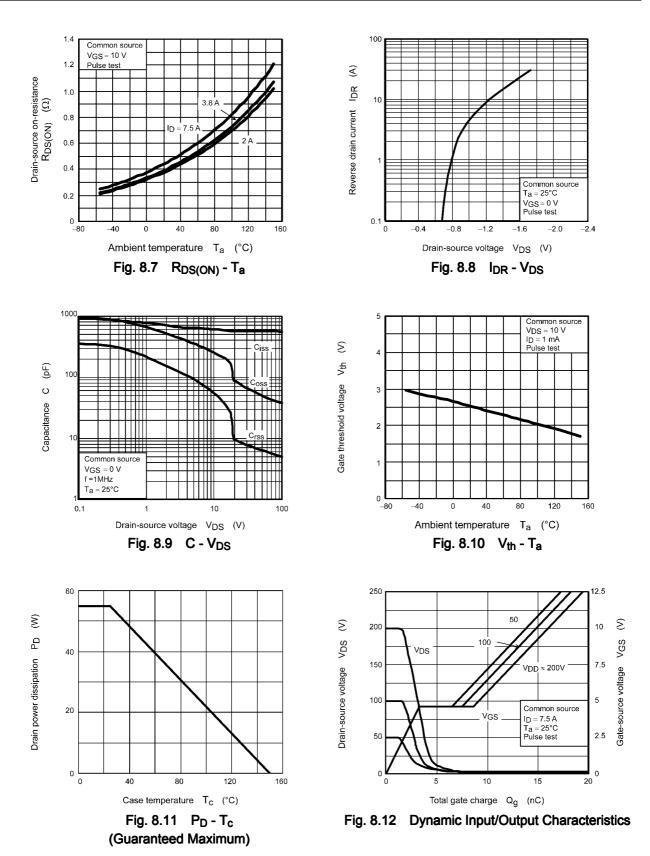
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Diode forward voltage	V <sub>DSF</sub>	I <sub>DR</sub> = 7.5 A, V <sub>GS</sub> = 0 V	_	—	-1.7	V
Reverse recovery time	t <sub>rr</sub>	I <sub>DR</sub> = 7.5 A, V <sub>GS</sub> = 0 V	_	150	_	ns
Reverse recovery charge	Q <sub>rr</sub>	-dI <sub>DR</sub> /dt = 100 A/μs		0.8	_	μC
Peak reverse recovery current	۱ <sub>rr</sub>		_	11	_	А

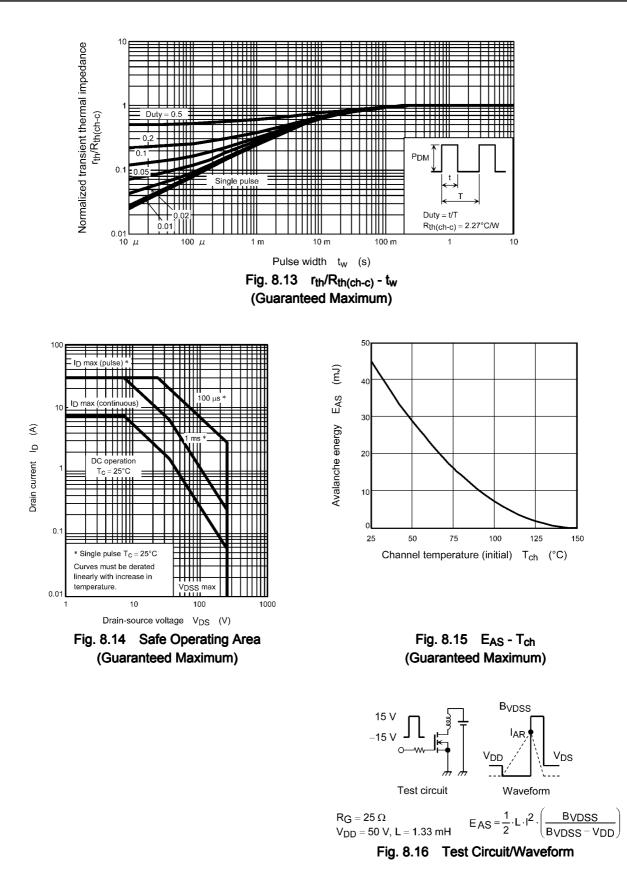
### 7. Marking



### 8. Characteristics Curves (Note)



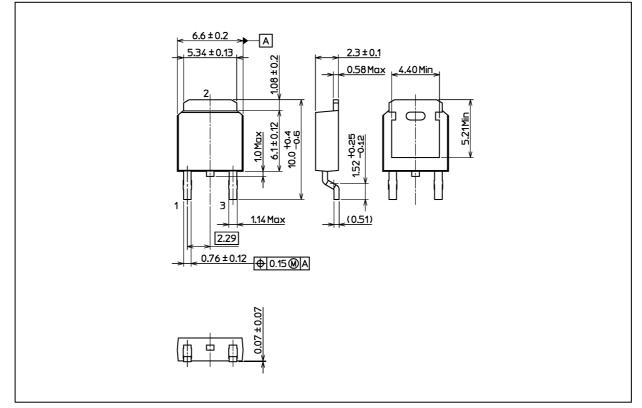




Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

### **Package Dimensions**

Unit: mm



Both products are compliant with the JEDEC: TO-252 Package specification. Please contact the Toshiba sales representative for further details.

Weight: 0.36 g (typ.)

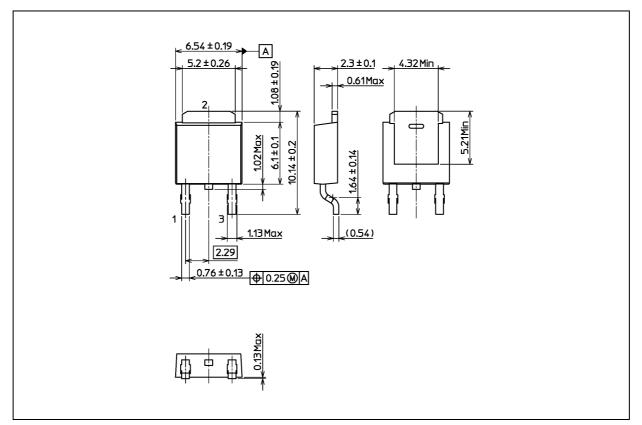
	Package Name(s)
JEDEC: TO-252	
TOSHIBA: 2-7K1S	
Nickname: DPAK	



### TK8P25DA

### **Package Dimensions**

Unit: mm



Both products are compliant with the JEDEC: TO-252 Package specification. Please contact the Toshiba sales representative for further details.

Weight: 0.389 g (typ.)

	Package Name(s)
JEDEC: TO-252	
TOSHIBA: 2-7N1S	
Nickname: DPAK	

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